DESCRIPTION:

With high ability to withstand

Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

[redacted]

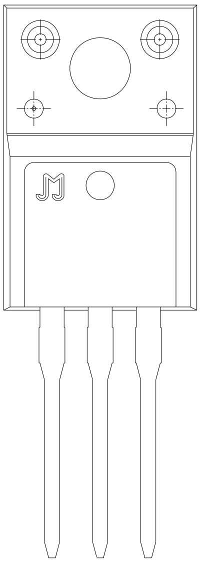
[redacted]

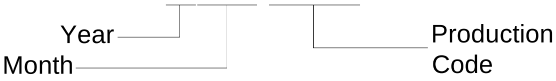
ORDERING INFORMATION

J CT 6 16 F H

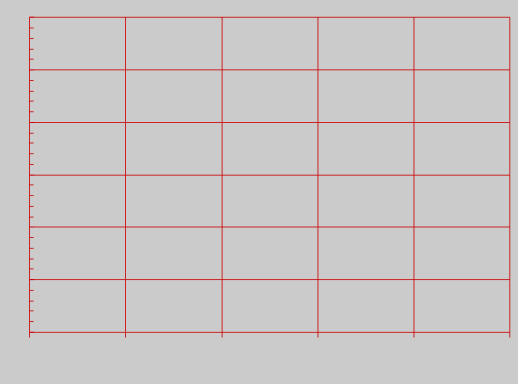
- J: JieJie Microelectronics Co., Ltd.
- CT: SCRs
- 6: 6:V_{DRM} /V_{RRM} ≥ 600V
- 16: $I_{T(RMS)}$:16A
- F: F:TO-220F(Ins)
- H: High junction temperature

MARKING





Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature

ORDERING INFORMATION

Date	Revision	Changes
Jun.15, 2023	A.1.0	Last update
Oct.17, 2022 ∃ Ǵ0¾	Ⱦ	

PACKAGE MECHANICAL DATA

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